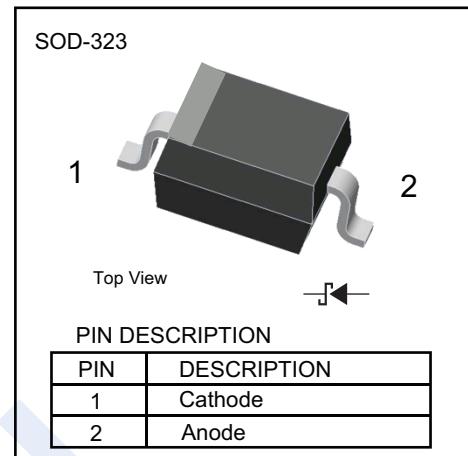


Schottky Diodes

PMEG1020EA

■ Features

- Forward current: 2A
- Reverse voltage: 10V
- Ultra low forward voltage
- Very small plastic SMD package.



■ Maximum Ratings Ta=25°C

Parameter	Symbol	Value	Unit
Continuous reverse voltage	V _R	10	V
Continuous forward current T _{sp} ≤55°C	I _F	2	A
Repetitive peak forward current t _p ≤1ms; δ≤0.5	I _{FRM}	3.2	
Non-repetitive peak forward current t _p =8ms square wave	I _{FSM}	9	
Thermal resistance from junction to ambient Note 1	R _{thJA}	450	°C/W
Note 2		210	
Thermal resistance from junction to solder point Note 3	R _{thJS}	90	
Junction temperature	T _J	150	°C
Storage temperature	T _{STG}	-65 to +150	
Operating ambient temperature	T _{amb}	-65 to +150	

Note: 1.Refer to SOD-323 standard mounting conditions.

2.Device mounted on an FR4 printed-circuit board with copper clad 10x10mm.

3.Solder point of cathode tab.

■ Electrical Characteristics Ta = 25°C unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V _R	I _R = 100 μA	10			V
Forward voltage	V _F	see Fig.1; note 1 I _F =0.01A I _F =0.1A I _F =1A I _F =2A			130 200 350 450	mV
Reverse current	I _R	see Fig.2; note 2 V _R =5V V _R =8V V _R =10V			2 2.5 3	mA
Diode capacitance	C _D	V _R =5V, f=1MHz; see Fig.3			45	pF

Note 1. Pulse test: t_p=300μs; δ=0.02.

2. For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses (P_R) are a significant part of the total power losses.

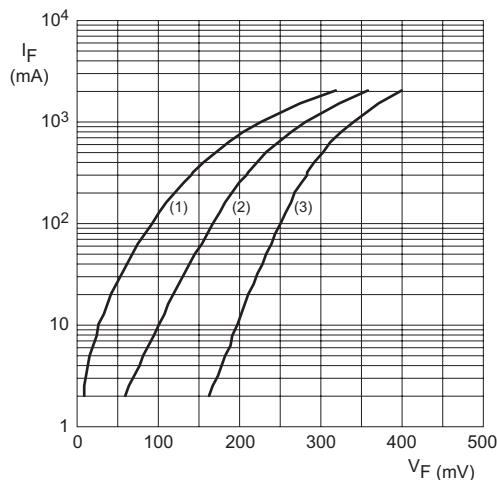
■ Marking

Marking	E2
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Schottky Diodes

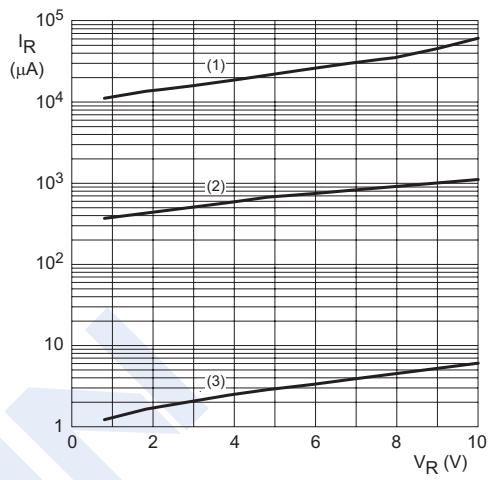
PMEG1020EA

■ Typical Characteristics



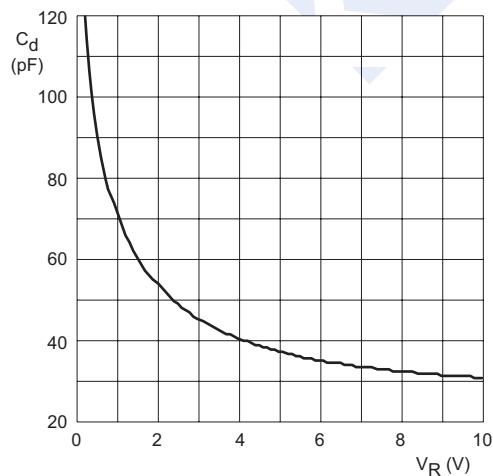
(1) $T_{amb} = 85 \text{ }^{\circ}\text{C}$.
 (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
 (3) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.

Fig.1 Forward current as a function of forward voltage; typical values.



(1) $T_{amb} = 85 \text{ }^{\circ}\text{C}$.
 (2) $T_{amb} = 25 \text{ }^{\circ}\text{C}$.
 (3) $T_{amb} = -40 \text{ }^{\circ}\text{C}$.

Fig.2 Reverse current as a function of reverse voltage; typical values.



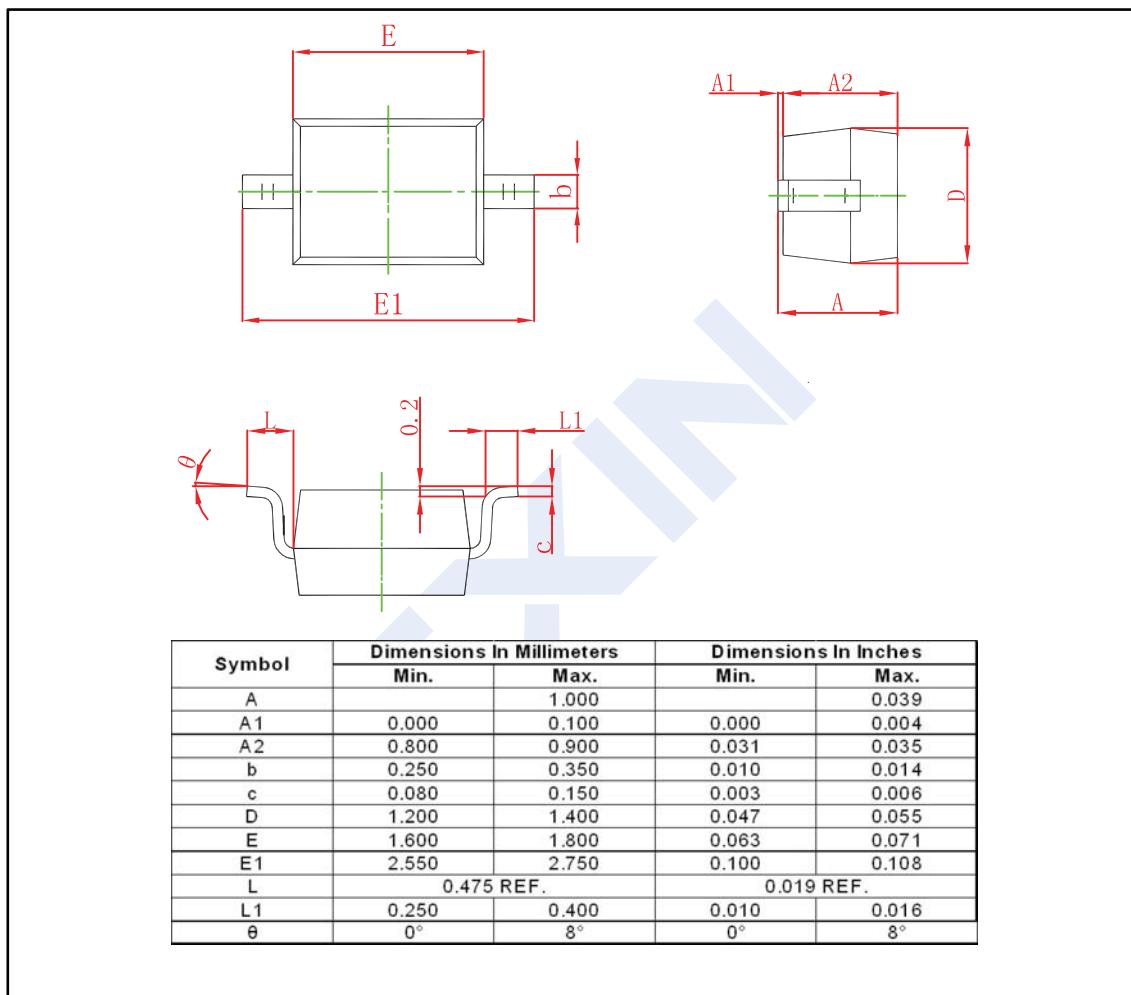
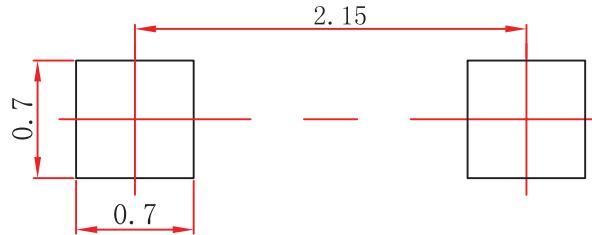
$f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$.

Fig.3 Diode capacitance as a function of reverse voltage; typical values.

Schottky Diodes**PMEG1020EA****■ Package Outline Dimensions**

Plastic surface mounted package; 2 leads

SOD-323

**■ The Recommended Mounting Pad Size****Note:**

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.